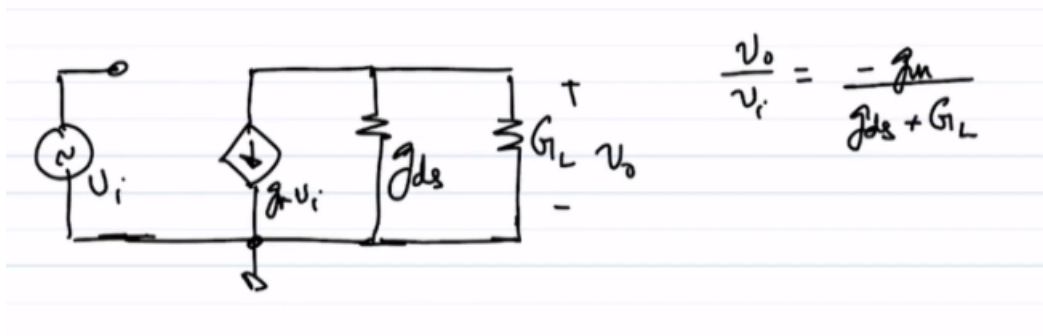


Course name- Analog VLSI Design (108104193)
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Department – Electrical Engineering
Institute – Indian Institute of Technology Kanpur
Week- 8
Lecture- 23

Now, welcome back, this is lecture 23. So, we were discussing in the previous lecture, the effects of effects of Y22 or GDS to our common source amplifier and we saw that, we saw that if we incorporate the effect of non-infinite output impedance or non-zero output conductance, right. So, if this is GDS grounded in our common source amplifier, this was the, this becomes the model and if I have an output load marked as G_L and we are taking the output across the output load, what do we observe? We observed that V_0 over V_i became minus G_M over G_{DS} plus G_L and naturally this is a lower value of gain than that we have gotten in the absence of GDS.



So, what was the solution? The solution that we came up with was use a current buffer, right. So, what is the current buffer? Again, a current buffer is a contraption that helps in pushing the current from a non-ideal current source to a load without the effect of loading, right. So in our case, our ideally, in our case, so this non-ideal current source was this section of G_M , V_i and G_{DS} , right.

This was a non-ideal current source, we have a load R_L or G_L , let me call this as R_{DS} , R_{DS1} , let me call this G_{M1} just to ensure that we are using the right consistent notations from previous lecture, right. So what do we need to do? We needed to, we needed to put a current buffer in between. So we needed to put a current buffer in between so that once we connect these, the amount of current that flows in, so this is G_M times V_i or in this case the amount of current that flows in should be minus G_M times V_i , right. So, the

approximately minus GM times V_i and that was possible only if the looking in impedance, right.

So, R_{in} would have been approximately 0 or in other words R_{in} is much much less than R_{DS1} , right. So this was the one of the bare minimum requirements of a current buffer. What was the other requirement? The other requirement for a current buffer obviously is the fact that the output impedance R_{out} , right, has to be much much greater than R_L because a current buffer is nothing but a current controlled current source, ok. So and how did we do this? We had already seen that what is a current buffer? A common gate amplifier is a, can act like a current buffer and we and then we said that is, so now what we need to do is to replace this block, right, replace this block with a common gate, correct. So again what is the incremental model of our common gate amplifier? So now what we can do? We can put, this becomes $GM_1 V_i$, this is GDR, let me call this R_{DS1} , R_{DS1} we have the load R_L and we had to put a common gate amplifier and we had used a common gate amplifier before and what is it? It is nothing but a, nothing but a contraption who is using a MOSFET whose incremental gate is grounded, right, whose gate is incrementally grounded and if we call this node as V_s , this current becomes GM times minus V_s because gate is grounded and just like any MOSFET we cannot neglect the output resistance, right, anymore because we now know that the output resistance is a reality, right and we connect this here and this becomes our Enaught, ok.

And then we further saw that, then what did we further see? We further saw that the short circuit current, the equivalent, not an equivalent model for this, so this is R_L , we call this I_{sc} and this R , this R_{out} , so not an equivalent model for this was I_{sc} was almost equal to GM_1 times V_i under the condition that, under what was the condition? If the looking in impedance, right, looking up impedance into the source of the common gate amplifier would have been much, much lesser than R_{DS1} , right. So if, whatever this R_{in} was, if R_{in} is much, much less than R_{DS1} , so in other words this translates to i.e., if GM_1 i.e.,

what was the looking in impedance? Looking in impedance was 1 over GM_1 plus G_{DS} , sorry, GM_2 plus G_{DS2} . This is the looking in impedance when the output was short circuited, right, so because we are trying to figure out what I_{sc} was, so that is an important thing that you should keep in mind. So when this looking up impedance, this is R_{in} was much, much lesser than R_{DS1} , right, so this was the requirement, right. So this is R_{in} when V_0 is 0, so that is an important consideration because otherwise the R_{in} will be different, ok. And what was R_{out} ? And we also saw that R_{out} was the summation of these two resistances, summation of R_{DS1} and R_{DS2} which naturally should appear but we had one additional term and the additional term was, the additional

term was GM2 times RDS2 times RDS2, correct.

$$i_c \approx g_m v_i \quad (\text{if } |K_{in}| \ll R_{DS1} \text{ when } v_o = 0)$$

$$\text{i.e. } \frac{1}{g_m + g_{DS2}} \ll R_{DS1}$$

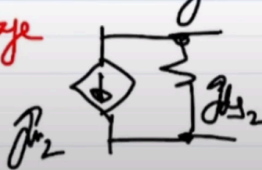
$$R_{out} = R_{DS1} + R_{DS2} + (g_m R_{DS2}) R_{DS1}$$

And then we further saw that, we further argued that it is expected that in saturation this term will be much, much greater than 1, GM2 times RDS2 because ultimately in saturation we want an amplifier to behave like, a transistor to behave like a, like almost like a current controlled, voltage controlled current source which means its output impedance should be closer to infinity. So, uncertainty is not possible but which means the output impedance should be very high and also we are expecting GM to be very high, so we are expecting GM times R to be very high, so it is expected that GM times R should be much greater than 1. If that is the case, in saturation your R out almost becomes equal to GM2 RDS2 times RDS1, right, right, ok. So, this is assuming GM2 RDS2 is much, much greater than 1, ok. So, now couple of jargons, so in a common source, in an amplifier, right, in an amplifier if I go back to this, so the common source amplifier model, right, so in the absence of, right, so in a, when GL is equal to 0, right, when GL is equal to 0, i.e. RL is equal to infinity,

Intrinsic gain of the current buffer on the C.G. stage

$$R_{out} \approx (g_m R_{DS2}) R_{DS1} \quad (\text{Assuming } g_m R_{DS2} \gg 1)$$

Intrinsic gain of the block



what is V_0 over V_i ? V_0 over V_i will be minus GM_1 times minus GM_1 by GDS_1 , correct, right. So what does this, what does this mean? It essentially means that even if your load is infinite, you are not getting infinite gain, right. In an ideal common source amplifier, if it were an ideal voltage control current source, then if we had an infinite load, if R_L would have been infinity, the voltage across that infinite load should also have been infinity. But in this case clearly that is not possible because the transistor does not have an infinite output impedance, right. So even in the absence of R_L , you are going to get a finite gain.

And this gain which is limited by the characteristics of the transistor itself is an intrinsic property of the transistor and we call this the intrinsic gain, right. So essentially we call GM_1 over GDS_1 to be intrinsic gain of a transistor, okay. So what is the intrinsic gain of this guy? What is the intrinsic gain of this guy? The intrinsic gain of that guy is basically the GM associated with that block times the impedance associated or the resistance associated with that block, right. So what is that intrinsic gain? So this essentially becomes intrinsic gain of block GM_2 , essentially this becomes the intrinsic gain of this contraption. So why am I saying all these things? I am saying all these things because it seems like the output impedance, right, output impedance of this contraption, so this output impedance or in other words the output impedance looking here, right, in the absence of the current buffer would have been R_{DS1} .

In the presence of current buffer, so in the absence of current buffer the output impedance would only have been R_{DS1} . In the presence of current buffer it seems like the output impedance has gotten amplified by the intrinsic gain of the current buffer, right. So this is the intrinsic gain of, this is the intrinsic gain of the current buffer or the common gate stage, correct. So this is a very important property, this is a very important property that you will often see in many places that in order to increase the output impedance of an amplifier often we put, we pass the current that is coming out of a common source stage to a common gate stage, right, so that the output impedance increases and this contraption is also called a gas code block, right. So this is also called, let me use a different page to talk about this.

So this the current buffer, the combination of a common source and a common gate stage to increase the output impedance is also called a gas code configuration, gas code. Please note the spelling is C-A-S-C-O-D-E not cascade, the gas code configuration, ok. So many times we will hear people saying why do not you use gas code, moment you say that you have a low output impedance you might hear people say why do not you use gas code. So gas code by that essentially what one means is why do not you pass the current from the common source stage to a common gate stage, right, ok. So now that we know what this is at least what the incremental circuit looks like we need to then take the next

step and see what will be the circuit look like when we replace the incremental equivalence with the MOSFET, right.

Ultimately we have to put the circuit together with the MOSFET, so let us do that, right. So let me quickly sketch the incremental equivalent once again. So this is V_i , right. So this is the gate of the first MOSFET, so this is V_{m1} times V_i and you have this output impedance G_{ds1} , then the gate of the second MOSFET is grounded, right. So this is V_{g2} is grounded, so this is $G_{m2} V_{g2} - V_s$, V_s and we have V_{ds2} and this output is obviously connected to a R_L , ok.

So now let us replace this stuff with the, so let me put the R_L on top so that I can save some space here, right. Let me put the R_L here, ok. So now what is the basic thing we need to do? So basically wherever you see this contraption you replace that with the MOSFET. So here comes one MOSFET, right. So let us call this M_1 .

Again what do you have on top of this M_1 ? You have another MOSFET, let us call this M_2 , correct and on top of that what do you have? You have a resistance R_L , right and now we need to bias, right. So how do you bias? M_1 is a common source stage. So how do you bias a common source stage? We know it by now, we have done it multiple times. So this becomes the common source bias, right. So let us call this V_{gu1} , ok.

How would you bias the transistor M_2 ? So clearly you cannot leave it floating. Can you keep it grounded? I cannot keep it grounded because of what? Because ultimately I need to bias the transistor in such a way that some current flows, right. We need some current, let us say some current I_{naught} to flow in this stack, right. So by the way before we proceed, can you tell me who is setting the current in this stack? Clearly the current in this stack will be set by M_1 . So what do I mean when I say who is setting the current in this stack? What I am essentially saying is which one is, on what factors does I_{naught} depend on? What are the primary factors on which I_{naught} depend on? So what does I_{naught} depend on in a transistor? It depends on, primarily it depends on the V_{gs} provided the transistor is in saturation.

Now as a designer we have to ensure that the transistor actually remains in saturation, right. So we can walk backwards and we can assume to start off that the transistor is in saturation and since I_{naught} depends on V_{gs} , so we can identify which is the transistor that is setting the V_{gs} , right. So in this case M_1 , the gate of M_1 is V_{gq} , what is the source of M_1 ? The source of M_1 is grounded. So the V_{gs} of M_1 is V_{gq} which we are setting separately, right. So since we are setting separately the V_{gs} of M_1 , the current I_{naught} will be determined by the V_{gs} of M_1 .

Now one might argue that what about the V_{gs} of M_2 , right. What about the V_{gs} of M_2 ? Is M_2 V_{gs} setting the current? I would argue no because, so let me take you back couple of lectures where we were discussing this. Let us assume that we need to bias this transistor M_2 with a constant current source of value I_{naught} . How do you go about biasing this? How do you go about biasing this? Basically this will auto bias as long as we ensure that the gate of M_2 is of certain value, correct. So we need to ensure that gate of M_2 is of some V_{gq2} , some value V_{gq2} , right.

And what will that value be? So for this we need to ensure that there is at least some voltage across I_{naught} , right. There should be some voltage across this current source I_{naught} otherwise the I_{naught} might start off and whatever that some voltage might be is a specification for the I_{naught} . And let us assume that specification is $V_{I_{naught}min}$, right. If this is $V_{I_{naught}min}$, what will be the voltage required at V_{gq2} ? So clearly your $V_{gq2} - V_{I_{naught}min}$ will be what? Will be the threshold voltage for M_2 plus the overdrive for M_2 which means V_{gq2} has to be what? It has to be at least $V_{threshold2} + V_{overdrive2} + V_{I_{naught}min}$, correct. Okay, so this we already had decided and what did we decide on the on how to bias R_L ? I mean this is the simpler part, we can simply say that this is connected to V_{DD} and as long as V_{DD} is high enough we need to ensure that we can ensure that M_2 remains in saturation, right.

So that is the easier part because here the voltage is $I_{naught} R_L$ $V_{DD} - I_{naught} R_L$. Okay, as long as we ensure that $V_{DD} - I_{naught} R_L$ is greater than $V_{gq2} - 1$ threshold voltage we are good, right. So fine, so now why did I come back to this? This we had already discussed but the reason I came back to this is what is our cascode stage now? What is this I_{naught} now? This I_{naught} is now instead of I_{naught} we have a transistor and what is that transistor? We have the transistor M_1 , right. So let me draw that. So instead of I_{naught} we have the transistor M_1 which is probably biased with the some voltage V_{gq1} .

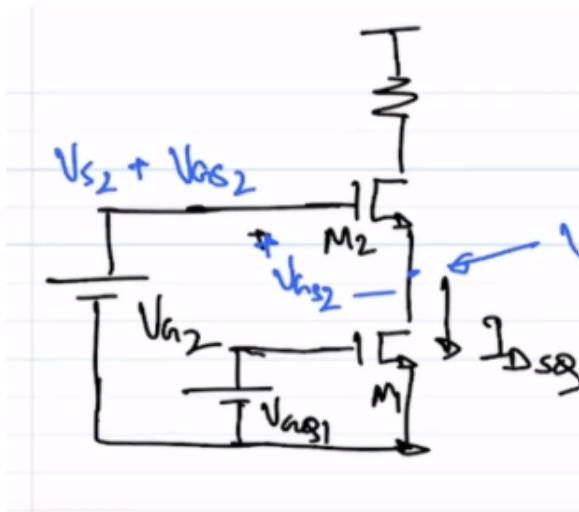
If this transistor is in saturation what will be this current? This current will be some I_{naught} or some I_{ds} , I_{dsq} , right, corresponding to I_{naught} , corresponding to M_1 , right. Okay, so then so now can you tell me what is the minimum voltage that is required to keep M_1 in saturation at this node? What is the minimum voltage? So this node let me call it V_s , right, or let me call this V_{s2} , right, because it is the source of M_2 . So let me call this V_{s2} . What is $V_{s2}min$? $V_{s2}min$ will be $V_{gq1} - \text{threshold voltage of the first transistor}$, right. This has to be $V_{gq1} - \text{threshold voltage of the first transistor}$.

Anything above this is fine but you cannot go below this, right. Fine. So if this is the

requirement, this is the requirement of V_{s2} , what has to be the requirement of this guy? What has to be the requirement of V_{g2} ? V_{g2} has to be $1 V_{gs}$ above V_{s2} , right. So this, note that this voltage drop is V_{gs2} . So this voltage V_{g2} has to be V_{s2} plus V_{gs2} .

What is V_{gs2} ? What is V_{gs2} ? V_{gs2} has to be equal to, this is we saw it here, right. So V_{gs2} has to be equal to $V_{\text{threshold}}$ voltage of the second transistor plus $V_{\text{over drive}}$ of the second transistor. So what does V_{g2} need to be? Therefore V_{g2} needs to be V_{s2} plus this, right. So what is V_{g2} ? V_{g2} , let me write it in a different line so that it makes sense. So your V_{g2} has to be, since V_{g2} is V_{s2} plus V_{gs2} , this has to be $V_{s2} \text{ min } V_{gs}$.

So this is, so V_{g2} has to be this which in other words V_{g2} has to be at least greater than V_{g2} has to be greater than equal to $V_{s2} \text{ min } V_{gs2}$ for a current of I_{ds} cube, right, for a current of I_{ds} cube, right. So this is equal to V , I just plug in the values so this becomes $V_{gs1} \text{ min } V_{\text{threshold}} \text{ voltage } 1 \text{ plus } V_{gs2}$ which is $V_{\text{threshold}} \text{ voltage } 2 \text{ plus } V_{\text{over drive}}$, correct. In other words this is equal to what? $V_{\text{over drive}}$ of the first transistor of M_1 , right. So $V_{\text{over drive}}$ of the first transistor plus $V_{\text{over drive}}$ of the second transistor M_2 plus the threshold voltage of the second transistor, right. So means that V_{g2} has to be greater than equal to this.



As long as we can ensure that V_{g2} is greater than equal to this under quiescent state, under quiescent state at least we can ensure that the transistor M_1 is in saturation. Why do I say M_1 ? The reason I say M_1 is let us assume that V_{g2} is lower than this value, ok. So let us assume V_{g2} is lower, right. So let us assume after doing all the maths we found out that, let us assume, we found that assume threshold voltage of 1 and threshold

voltage of the second transistor are 1 volt. Let us assume the over drive voltage is also 1 volt for both the transistors.

$$V_{GS2} = V_{TH2} + V_{OV2}$$

$$V_{S2}(\min) = V_{GS1} - V_{TH1}$$

$$V_{GS2} = V_{S2} + V_{GS2} / I_{DSQ}$$

$$V_{GS2} \geq V_{S2}(\min) + V_{GS2} / I_{DSQ}$$

$$= \underbrace{V_{GS1} - V_{TH1}} + V_{TH2} + V_{OV2}$$

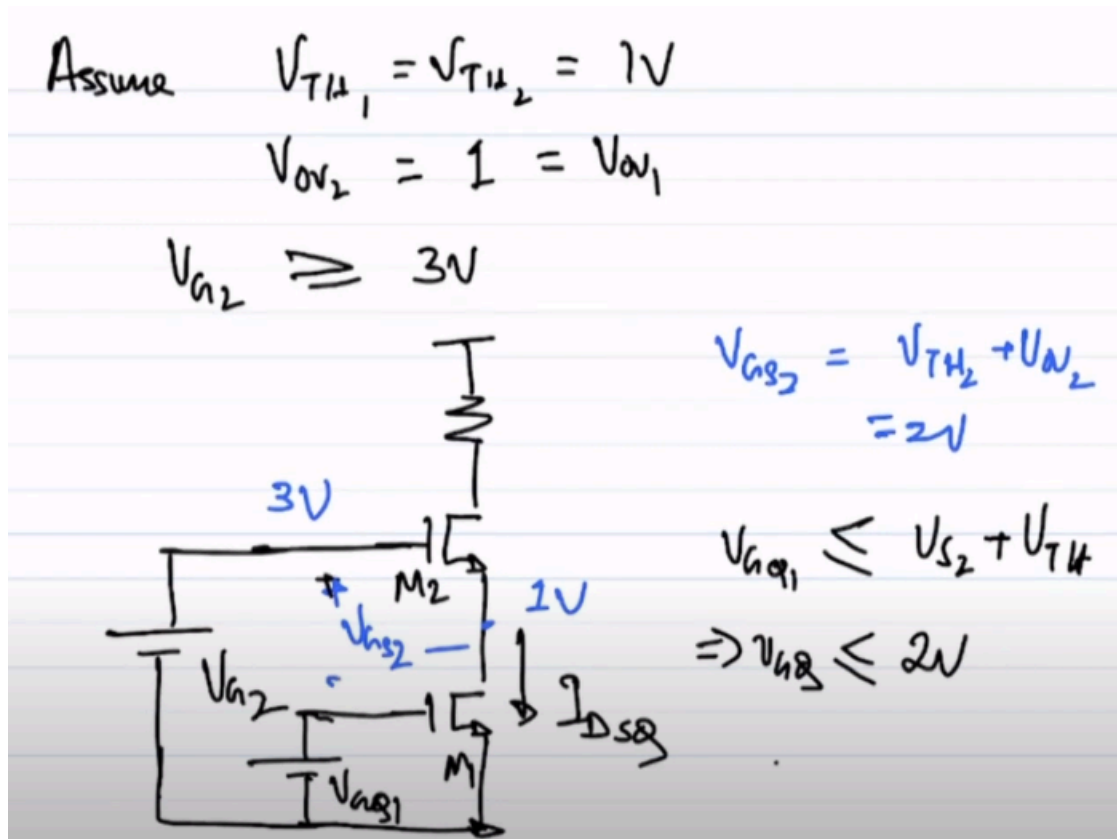
$$\Rightarrow V_{GS2} \geq V_{OV1} + V_{OV2} + V_{TH2}$$

Did not be the case because note that over drive is a function of the size of the transistor But to make our life simple let us assume that the over drive of both the transistors are also equal to 1 volt, right. So if that is the case, what do you need to ensure V_{G2} to be? So V_{G2} should be at least greater than V_{TH1} , 1 volt, V_{OV2} , 2 volt and V_{TH2} is 2 volt, 1 volt which means this should be at least greater than 3 volt, correct. So what happens if let us say this is not 3 volt, so let me put the values together once more. So let us assume that, what did we assume? Let us say this is equal to 3 volt, so this is 3 volt, I could use a different color maybe, ok. If this is 3 volt, what is V_{GS2} ? V_{GS2} is 1 over drive, V_{GS2} is threshold voltage of 2 plus over drive voltage of 2 which is 2 volt.

If the gate is of 3 volt, threshold voltage V_{GS2} is 2 volt, what is the source of M_2 ? This is 1 volt. So in order to keep let us say M_1 in saturation, right, in order to keep M_1 in saturation what we need? This is something that we have discussed earlier but not in this context. So what we need? What we need V_{GS1} to be? So V_{GS1} has to be less than V_{S2} plus 1 threshold voltage, correct? So which means this has to be implies V_{GS1} has to be less than 2 volt, right? So let us assume, let us pick a number, let us put it at 2

volt. Why would pick a number? Let us put it at 2 volt.

So let us say this is 2 volt, ok. So let us remove this, ok. So now tell me, ok tell me one more thing before we proceed. What do you think has to be the value at the drain of M 2? At least it has to be greater than the drain voltage of M 2 minus 1 threshold voltage of M 2, right? So which means that this has to be at least 2 volt or higher. Let us pick a different number, let us not keep it right at the edge.



Let us say this is 2.5 volt or let us say this is 3 volt, ok. What is the drop across R L? The drop across R L is I_{dsq} times R L, right? So that might be some value and let us assume that we have chosen V d d to have an appropriate value to keep M 2 in saturation, ok. So now let me, now tell me what is going to happen if I reduce the voltage, gate voltage of M 2 from 3 volt to let us say 2.5 volt. Ok even before that tell me what is going to happen if I increase the gate voltage of M 2 by let us say plus 100 millivolt, 0.

14 volt. What is going to happen to the circuit? Will the current in the network change? To the first order will the current in the network change? So here in you have to

understand who is setting the current in the network. So who, if the transistor, if both the transistors M_1 and M_2 are in saturation, right, if both the transistors are in saturation is I_{dsq} likely to change? Clearly not. I mean you can neglect the effect of, you can neglect the effect of channel length modulation for the purpose of this analysis, right? So if we neglect the channel length modulation and if M_1 and M_2 are in saturation, right, so I_{dsq} will depend on, depends solely on the T_{gs1} , correct? So neglecting, if we neglect channel length modulation, if CLM is neglected, right? So the current in I_{dsq} , the current I_{dsq} solely depends on the V_{gs} of M_1 . Why? Because the source of M_1 is grounded, you cannot change the source voltage, but the gate of the M_1 is dependent on you, you are driving the gate, right? So essentially I_{dsq} is dependent on, is only dependent on the V_{gs} of M_1 , which means for M_2 , M_1 behaves like an ideal current source. So if M_1 acts like an ideal current source for M_2 , changing the gate voltage of M_2 should not change the current in that stack, correct? If changing gate voltage of M_2 does not change the current, what is the only likely scenario? The only likely scenario is the V_{gs} of M_2 will not change, right? So essentially what I am trying to say is, if M_1 is, if M_1 and M_2 are in saturation, I_{dsq} depends only on M_1 and not on M_2 , right? Since it only depends on M_1 and not on M_2 , what is the implication? The implication is, this implies V_{gs} of M_2 , that is V_{gs2} is constant.

V_{gs2} does not change, even if you change the gate voltage of M_2 , right? So if V_{gs2} does not change, what does that mean? It means essentially that if V_{gs2} is increased, then V_{gs2} will also increase. By how much? By exactly the same amount, because if it does not increase by the same amount, right? What is going to happen? You will not have V_{gs2} to be constant, right? So this since V_{gs2} has to be constant due to constant current bias for M_2 , right? So what is going to happen here? So now coming back to the point, if the gate of M_2 goes up by 100 millivolt, the source of M_2 also has to go up by 100 millivolt. So this will also go up by 100 millivolt. If this goes up by 100 millivolt, will the current through M_1 change, neglecting channel length modulation? If you neglect channel length modulation, if you increase the drain, if you change the drain to source voltage of a transistor, should the current change? No. One might argue that it should change now because we have been including channel length, we have been including GDS, but again, you should understand that when to neglect something and when not to.

In this case, there will be some change, but that change will be miniscule with respect to the quiescent. Since the change will be miniscule with respect to quiescent, we can neglect the miniscule change. When you are doing incremental, you cannot neglect GDS because you cannot neglect anything with respect to 0. So again, coming back to the same point, if I circle back to wherever we started, what who is setting that source voltage of M_2 ? Clearly, the gate voltage of M_2 is setting the source voltage of M_2 .

The source voltage of M₂ is not constant. If I change, if I increase gate voltage of M₂, the source voltage of M₂ will also increase. Ok, great. So, this is all good, but what happens if I reduce the source voltage, if I go by minus 0.1 volt? By the same logic, what will happen? What will happen to the source of M₂? This will go by, this will also reduce by minus 1.

1 volt in order to keep the V_{GS} to same. But now let us turn our attention to M₁. What do you think is a biasing condition of, what do you think is the operating condition of M₁ now when the source or the drain of M₁ or the source of M₂ has reduced by 100 millivolt? Clearly, M₁ is not in saturation anymore, right? Because now the saturation condition of M₁ is getting violated, ok, right? So, what was the saturation condition of M₁? We had to ensure this condition and this condition is no longer valid if the source voltage falls from 1 volt to 0.9 volt. So, what is the solution? You cannot really, I mean, what is the reason of this problem? This problem arose because we were biasing the transistors right at the edge. We are biasing the transistors right at the edge of saturation.

For which transistor? For right at the edge for M₁, not for M₂, right? Because the way we took the values, note that the drain of M₂ is 3 volt. For M₂ to go out of saturation, we had to increase the gate voltage of M₂ to beyond 4 volts. Then only M₂ would have gone out of saturation. But in this case, if we bias that gate of M₂ to a lower voltage than 3 volt, it seems like M₁ will go out of saturation, right? So, since this is not a viable condition, so what we need to do? We need to ensure that we do not bias it right at the edge, we have to ensure that. We have to ensure that for a proper health of the transistor M₁, we have to ensure that the gate voltage of M₂ should be higher than 3 volts.

So, this is 2 volt, right? So, this has to be then greater than 3 volt. Let us pick another value, let us pick like 3.5 volt. Because if I and this was supposed to be 3 volt, right? So, this was 3 volt. By the way, who is setting the 3 volt? This 3 volt is set by because we expect a current of $I_{D S Q}$, this is $V_{D D}$, right? So, this voltage is $V_{D D} - R_L \times I_{D S Q}$ and let us assume that we have chosen $V_{D D}$ and $I_{D S Q}$ in such a way that this is 3 volt.

If this is 3 volt, I need to ensure that the gate of M₂ is not above 4 volt. So, we chose this to be about 3.5 volt, right? If this is 3.5 volt and under the conditions of P overdrive, whatever we chose, what will be this voltage? This will be approximately 1.

5 volt. If this is 1.5 volt, what do you think is the health of M₁? Even if this guy drops by, for some reason if the voltage at M₂ drops by 100 millivolt, this will drop by 100

millivolt and still we are good, right? Now, the reason why it should drop is, we will see later, right? You can have different temperature variations, you can have non-robust biasing, all those conditions because of which the voltage at the gate of, I mean voltages at various nodes can change, but we should always keep in mind that during design, we should not make a design which is just at the edge of working, right? We need to have some margin, we need to ensure that the transistors are not biased just at the edge of cut-off or just at the edge of saturation and hence we decided to, in this case we decided to increase that voltage, I mean bias the voltage of M₂ in such a way that both M₂ and M₁ are comfortably in saturation even if things change slightly, ok? Ok. Thank you.